

# 2SD1751

## Silicon NPN triple diffusion planar type

For power amplification

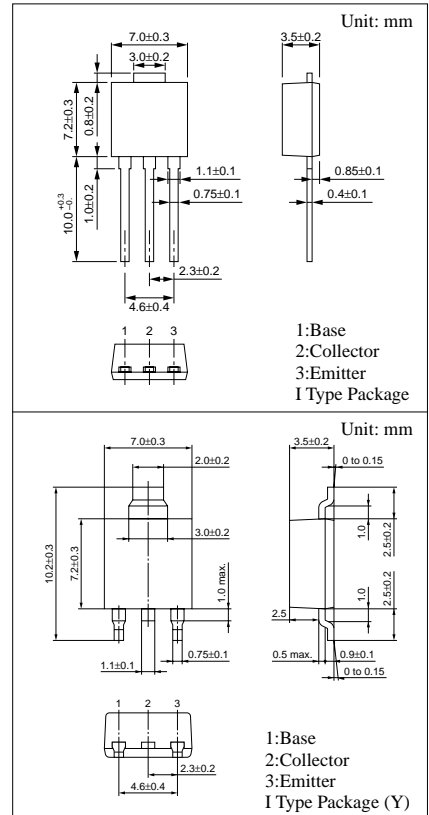
Complementary to 2SB1170

### Features

- High forward current transfer ratio  $h_{FE}$  which has satisfactory linearity
- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- I type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Rated	Unit
Collector to base voltage	$V_{CBO}$	60	V
Collector to emitter voltage	$V_{CEO}$	60	V
Emitter to base voltage	$V_{EBO}$	6	V
Peak collector current	$I_{CP}$	4	A
Collector current	$I_C$	2	A
Collector power dissipation	$P_C$	$T_C=25^\circ\text{C}$	15
		$T_a=25^\circ\text{C}$	1.3
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



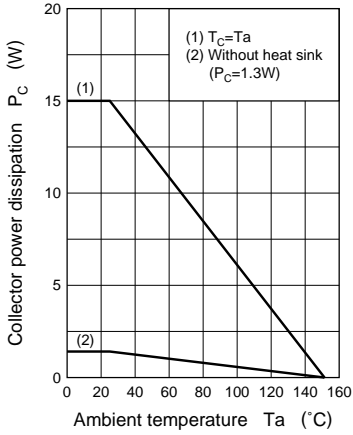
### Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CES}$	$V_{CE} = 60\text{V}, V_{BE} = 0$			200	$\mu\text{A}$
	$I_{CEO}$	$V_{CE} = 30\text{V}, I_B = 0$			300	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 6\text{V}, I_C = 0$			1	mA
Collector to emitter voltage	$V_{CEO}$	$I_C = 30\text{mA}, I_B = 0$	60			V
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = 4\text{V}, I_C = 0.1\text{A}$	35			
	$h_{FE2}^*$	$V_{CE} = 4\text{V}, I_C = 1\text{A}$	70		250	
Base to emitter voltage	$V_{BE}$	$V_{CE} = 4\text{V}, I_C = 1\text{A}$			1.2	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{A}, I_B = 0.2\text{A}$			2	V
Transition frequency	$f_T$	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}, f = 1\text{MHz}$		20		MHz
Turn-on time	$t_{on}$	$I_C = 1\text{A}, I_{B1} = 0.1\text{A}, I_{B2} = -0.1\text{A}$		0.2		$\mu\text{s}$
Storage time	$t_{stg}$			3.5		$\mu\text{s}$
Fall time	$t_f$			0.7		$\mu\text{s}$

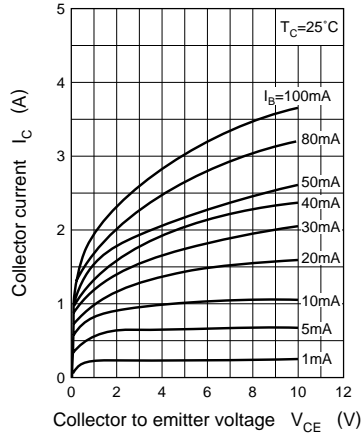
\* $h_{FE2}$  Rank classification

Rank	Q	P
$h_{FE2}$	70 to 150	120 to 250

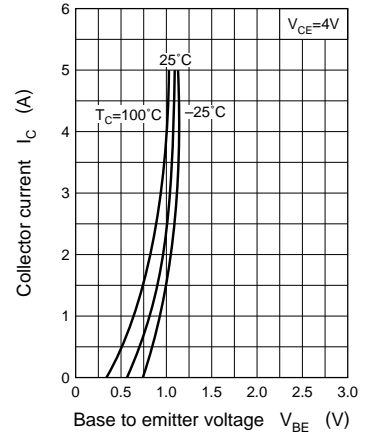
$P_C - T_a$



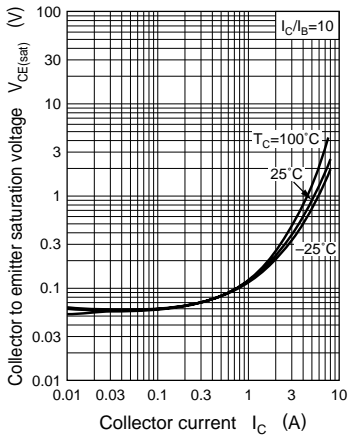
$I_C - V_{CE}$



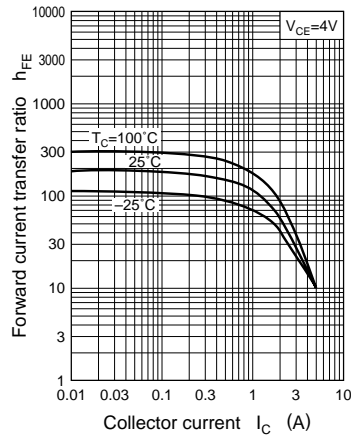
$I_C - V_{BE}$



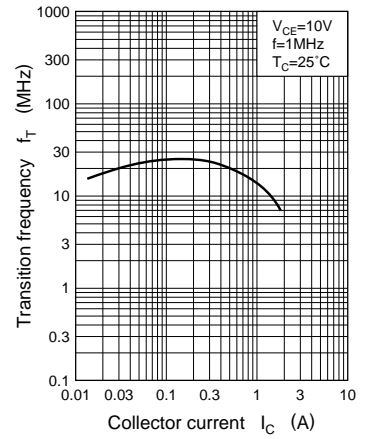
$V_{CE(sat)} - I_C$



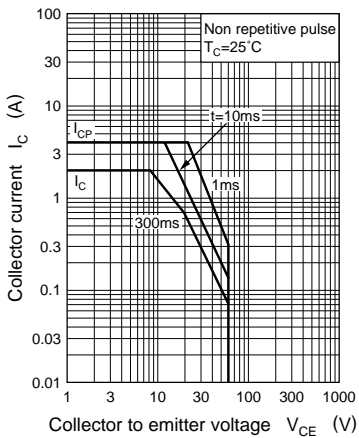
$h_{FE} - I_C$



$f_T - I_C$



Area of safe operation (ASO)



$R_{th(t)} - t$

